

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH367FK,TC7MH368FK

HEX Bus Buffer

TC7MH367FK Non-Inverted, 3-State Outputs**TC7MH368FK Inverted, 3-State Outputs**

The TC7MH367FK and TC7MH368FK are advanced high speed CMOS HEX bus buffers fabricated with silicon gate C²MOS technology.

They achieve the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

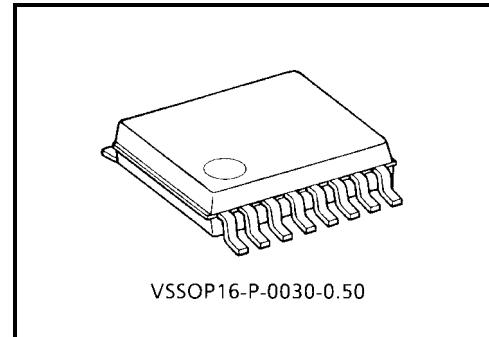
They contain six buffers; four buffers are controlled by an enable input (\bar{G}_1), and the other two buffers are controlled by another enable input (\bar{G}_2). The outputs of each buffer group are enabled when \bar{G}_1 and/or \bar{G}_2 inputs are held low; if held high, these outputs are in a high impedance state.

The TC7MH367FK is a non-inverting output type, while the TC7MH368FK is an inverting output type.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

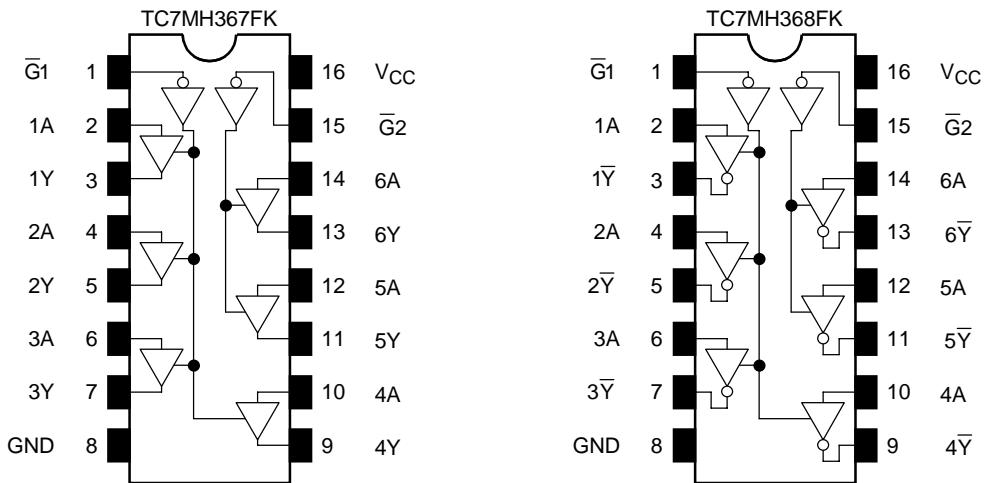
Features

- High speed: $t_{pd} = 3.8$ ns (typ.) ($V_{CC} = 5$ V)
- Low power dissipation: $I_{CC} = 4$ μ A (max) ($T_a = 25^\circ\text{C}$)
- High noise immunity: $V_{NIH} = V_{NIL} = 28\%$ V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: V_{CC} (opr) = 2~5.5 V
- Low noise: $V_{OLP} = 0.8$ V (max)
- Pin and function compatible with 74ALS367/368

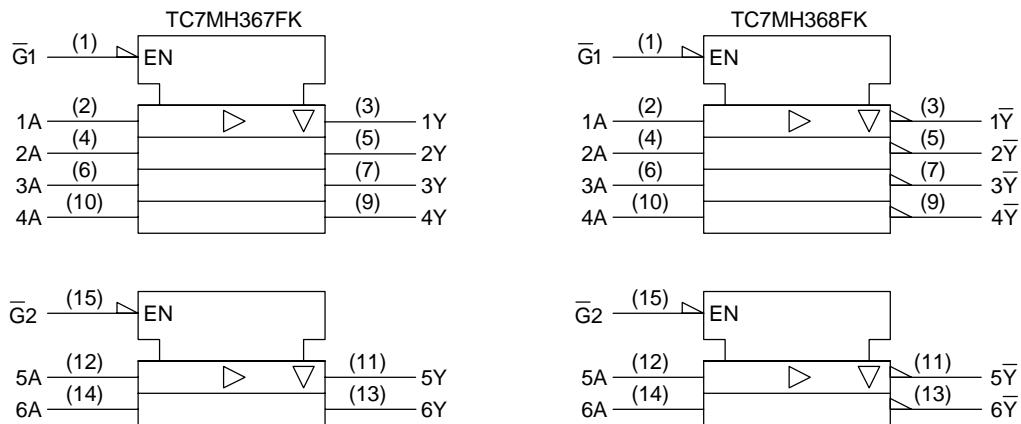


Weight: 0.02 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inputs		Outputs	
\bar{G}	A	Y (367)	\bar{Y} (368)
L	L	L	H
L	H	H	L
H	X	Z	Z

X: Don't care

Z: High impedance

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5~7.0	V
DC input voltage	V_{IN}	-0.5~7.0	V
DC output voltage	V_{OUT}	-0.5~ V_{CC} + 0.5	V
Input diode current	I_{IK}	-20	mA
Output diode current	I_{OK}	± 20	mA
DC output current	I_{OUT}	± 25	mA
DC V_{CC} /ground current	I_{CC}	± 50	mA
Power dissipation	P_D	180	mW
Storage temperature	T_{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2.0~5.5	V
Input voltage	V_{IN}	0~5.5	V
Output voltage	V_{OUT}	0~ V_{CC}	V
Operating temperature	T_{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~100 ($V_{CC} = 3.3 \pm 0.3$ V) 0~20 ($V_{CC} = 5 \pm 0.5$ V)	ns/V

Electrical Characteristics

DC Characteristics

Characteristics		Symbol	Test Condition	V _{CC} (V)	Ta = 25°C			Ta = -40~85°C		Unit	
					Min	Typ.	Max	Min	Max		
Input voltage	High level	V _{IH}	—	2.0	1.50	—	—	1.50	—	V	
				3.0~5.5	V _{CC} × 0.7	—	—	V _{CC} × 0.7	—		
	Low level	V _{IL}	—	2.0	—	—	0.50	—	0.50		
				3.0~5.5	—	—	V _{CC} × 0.3	—	V _{CC} × 0.3		
Output voltage	High level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	2.0	1.9	2.0	—	1.9	V	
					3.0	2.9	3.0	—	2.9		
					4.5	4.4	4.5	—	4.4		
				I _{OH} = -4 mA	3.0	2.58	—	—	2.48		
	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	4.5	3.94	—	—	3.80	V	
					2.0	—	0	0.1	—		
					3.0	—	0	0.1	—		
					4.5	—	0	0.1	—		
				I _{OL} = 4 mA	3.0	—	—	0.36	—		
				I _{OL} = 8 mA	4.5	—	—	0.36	—		
3-state output off-state current	I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND		5.5	—	—	±0.25	—	±2.50	μA	
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	—	—	±0.1	—	±1.0	μA	
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		5.5	—	—	4.0	—	40.0	μA	

AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	Ta = 25°C			Ta = -40~85°C		Unit	
			V _{CC} (V)	C _L (pF)	Min	Typ.	Max		
Propagation delay time (TC7MH367)	t _{pLH}	—	3.3 ± 0.3	15	—	5.9	8.3	1.0 10.0	
				50	—	8.4	11.8	1.0 13.5	
	t _{pHL}		5.0 ± 0.5	15	—	4.1	5.9	1.0 7.0	
				50	—	5.6	7.9	1.0 9.0	
	t _{pLH}	—	3.3 ± 0.3	15	—	5.3	7.5	1.0 9.0	
				50	—	7.8	11.0	1.0 12.5	
	t _{pHL}		5.0 ± 0.5	15	—	3.8	5.5	1.0 6.5	
				50	—	5.3	7.5	1.0 8.5	
3-state output enable time	t _{pZL}	R _L = 1 kΩ	3.3 ± 0.3	15	—	6.8	10.5	1.0 12.5	
				50	—	9.3	14.0	1.0 16.0	
	t _{pZH}		5.0 ± 0.5	15	—	4.8	7.2	1.0 8.5	
				50	—	6.3	9.2	1.0 10.5	
	t _{pLZ}	R _L = 1 kΩ	3.3 ± 0.3	50	—	9.9	13.6	1.0 15.5	
			5.0 ± 0.5	50	—	6.3	9.2	1.0 10.5	
	t _{pHZ}	(Note1)	3.3 ± 0.3	50	—	—	1.5	— 1.5	
			5.0 ± 0.5	50	—	—	1.0	— 1.0	
Input capacitance	C _{IN}	—	—	—	4	10	—	10 pF	
Output capacitance	C _{OUT}	—	—	—	6	—	—	— pF	
Power dissipation capacitance	C _{PD}	(Note2)	—	—	19	—	—	— pF	

Note1: Parameter guaranteed by design.

$$t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLM} - t_{pHLn}|$$

Note2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

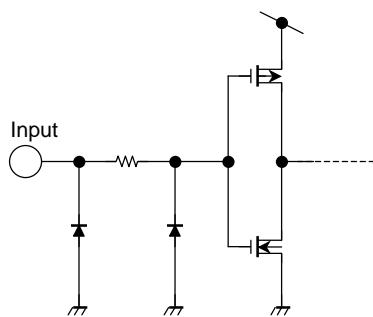
Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per bit)}$$

Noise Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	Ta = 25°C			Unit
			V _{CC} (V)	Typ.	Limit	
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.4	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLO}	C _L = 50 pF	5.0	-0.4	-0.8	V
Minimum high level dynamic input voltage V _{IH}	V _{IHD}	C _L = 50 pF	5.0	—	3.5	V
Maximum low level dynamic input voltage V _{IL}	V _{ILD}	C _L = 50 pF	5.0	—	1.5	V

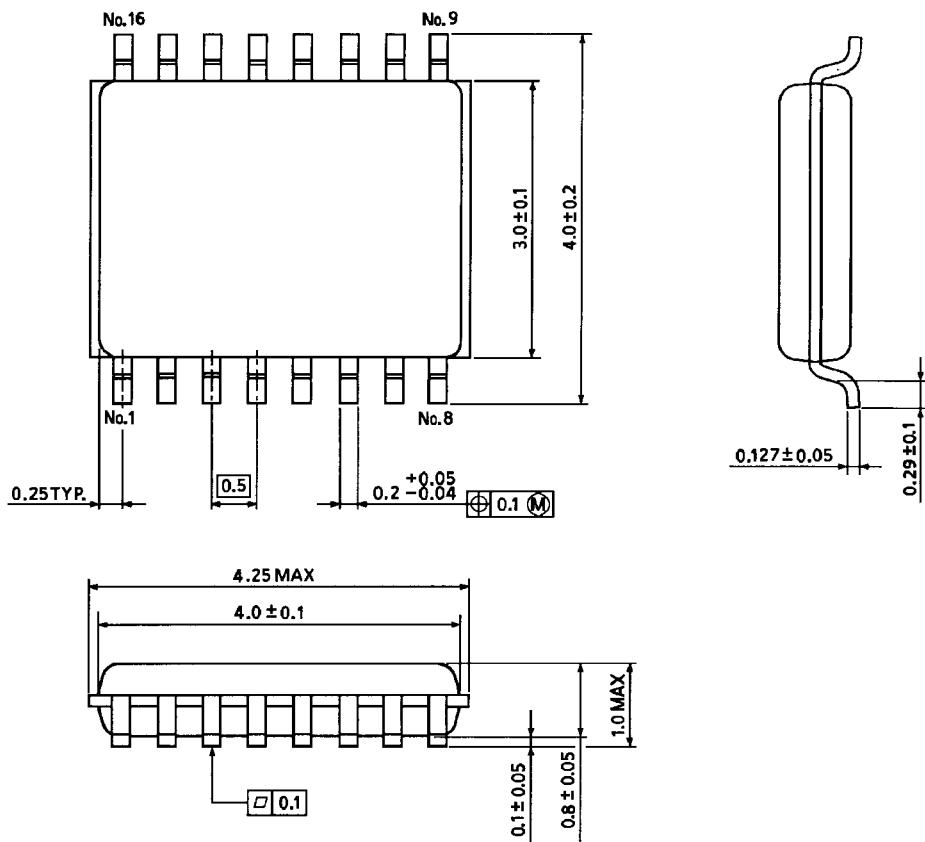
Input Equivalent Circuit



Package Dimensions

VSSOP16-P-0030-0.50

Unit : mm



Weight: 0.02 g (typ.)

RESTRICTIONS ON PRODUCT USE

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